Preferred Device

Switching Transistor

PNP Silicon

Features

• Pb–Free Packages are Available

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V _{CEO}	-40	Vdc
Collector-Base Voltage	V _{CBO}	-40	Vdc
Emitter-Base Voltage	V _{EBO}	-5.0	Vdc
Collector Current – Continuous	Ι _C	-600	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR–5 Board (Note 1) @T _A = 25°C Derate above 25°C	P _D	225 1.8	mW mW/°C
Thermal Resistance, Junction-to-Ambient	R_{\thetaJA}	556	°C/W
Total Device Dissipation Alumina Substrate, (Note 2) @T _A = 25°C Derate above 25°C	P _D	300 2.4	mW mW/°C
Thermal Resistance, Junction-to-Ambient	R_{\thetaJA}	417	°C/W
Junction and Storage Temperature	T _J , T _{stg}	-55 to +150	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

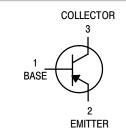
*Transient pulses must not cause the junction temperature to be exceeded. 1. FR-5 = $1.0 \times 0.75 \times 0.062$ in.

2. Alumina = $0.4 \times 0.3 \times 0.024$ in. 99.5% alumina.



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MARKING DIAGRAM



= Specific Device Code 2T Μ

= Date Code*

= Pb-Free Package

(Note: Microdot may be in either location) *Date Code orientation and/or overbar may vary depending upon manufacturing location.

ORDERING INFORMATION

Device	Package	Shipping [†]
MMBT4403LT1	SOT-23	3000 Tape & Reel
MMBT4403LT1G	SOT-23 (Pb-Free)	3000 Tape & Reel
MMBT4403LT3	SOT-23	10,000 Tape & Reel
MMBT4403LT3G	SOT-23 (Pb-Free)	10,000 Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

Preferred devices are recommended choices for future use and best overall value.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic			Min	Max	Unit
OFF CHARACTERISTICS					
Collector – Emitter Breakdown Voltage (Note 3)	$(I_{C} = -1.0 \text{ mAdc}, I_{B} = 0)$	V _{(BR)CEO}	-40	_	Vdc
Collector-Base Breakdown Voltage	$(I_{C} = -0.1 \text{ mAdc}, I_{E} = 0)$	V _{(BR)CBO}	-40	_	Vdc
Emitter-Base Breakdown Voltage	$(I_{E} = -0.1 \text{ mAdc}, I_{C} = 0)$	V _{(BR)EBO}	-5.0	_	Vdc
Base Cutoff Current	$(V_{CE} = -35 \text{ Vdc}, V_{EB} = -0.4 \text{ Vdc})$	I _{BEV}	-	-0.1	μAdc
Collector Cutoff Current	$(V_{CE} = -35 \text{ Vdc}, V_{EB} = -0.4 \text{ Vdc})$	I _{CEX}	-	-0.1	μAdc
ON CHARACTERISTICS					
DC Current Gain (Note 3) (Note 3)	$ (I_C = -0.1 \text{ mAdc}, V_{CE} = -1.0 \text{ Vdc}) \\ (I_C = -1.0 \text{ mAdc}, V_{CE} = -1.0 \text{ Vdc}) \\ (I_C = -10 \text{ mAdc}, V_{CE} = -1.0 \text{ Vdc}) \\ (I_C = -150 \text{ mAdc}, V_{CE} = -2.0 \text{ Vdc}) \\ (I_C = -500 \text{ mAdc}, V_{CE} = -2.0 \text{ Vdc}) $	h _{FE}	30 60 100 100 20	- - 300 -	_
Collector – Emitter Saturation Voltage (Note 3)	$(I_{C} = -150 \text{ mAdc}, I_{B} = -15 \text{ mAdc})$ $(I_{C} = -500 \text{ mAdc}, I_{B} = -50 \text{ mAdc})$	V _{CE(sat)}		-0.4 -0.75	Vdc
Base – Emitter Saturation Voltage (Note 3)	$(I_{C} = -150 \text{ mAdc}, I_{B} = -15 \text{ mAdc})$ $(I_{C} = -500 \text{ mAdc}, I_{B} = -50 \text{ mAdc})$	V _{BE(sat)}	-0.75 -	-0.95 -1.3	Vdc

SMALL-SIGNAL CHARACTERISTICS

Current-Gain - Bandwidth Product	$(I_{C} = -20 \text{ mAdc}, V_{CE} = -10 \text{ Vdc}, f = 100 \text{ MHz})$	f _T	200	-	MHz
Collector-Base Capacitance	$(V_{CB} = -10 \text{ Vdc}, I_E = 0, f = 1.0 \text{ MHz})$	C _{cb}	-	8.5	pF
Emitter-Base Capacitance	$(V_{BE} = -0.5 \text{ Vdc}, I_{C} = 0, f = 1.0 \text{ MHz})$	C _{eb}	-	30	pF
Input Impedance	$(I_{C} = -1.0 \text{ mAdc}, V_{CE} = -10 \text{ Vdc}, f = 1.0 \text{ kHz})$	h _{ie}	1.5	15	kΩ
Voltage Feedback Ratio	$(I_{C} = -1.0 \text{ mAdc}, V_{CE} = -10 \text{ Vdc}, f = 1.0 \text{ kHz})$	h _{re}	0.1	8.0	X 10 ⁻⁴
Small-Signal Current Gain	$(I_{C} = -1.0 \text{ mAdc}, V_{CE} = -10 \text{ Vdc}, f = 1.0 \text{ kHz})$	h _{fe}	60	500	-
Output Admittance	$(I_{C} = -1.0 \text{ mAdc}, V_{CE} = -10 \text{ Vdc}, f = 1.0 \text{ kHz})$	h _{oe}	1.0	100	μMhos
SWITCHING CHARACTERISTICS					
Dalay Time				15	

Delay Time	$(V_{CC} = -30 \text{ Vdc}, V_{EB} = -2.0 \text{ Vdc},$	t _d	-	15	
Rise Time	$I_{\rm C} = -150 \text{ mAdc}, I_{\rm B1} = -15 \text{ mAdc})$	t _r	-	20	ns
Storage Time	(V _{CC} = −30 Vdc, I _C = −150 mAdc,	t _s	-	225	ns
Fall Time	I _{B1} = I _{B2} = −15 mAdc)	t _f	-	30	115

3. Pulse Test: Pulse Width \leq 300 µs, Duty Cycle \leq 2.0%.

SWITCHING TIME EQUIVALENT TEST CIRCUIT

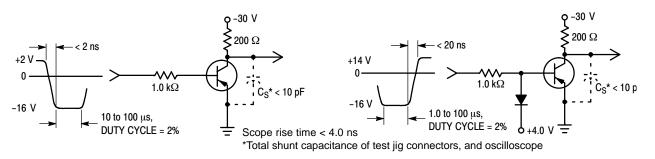
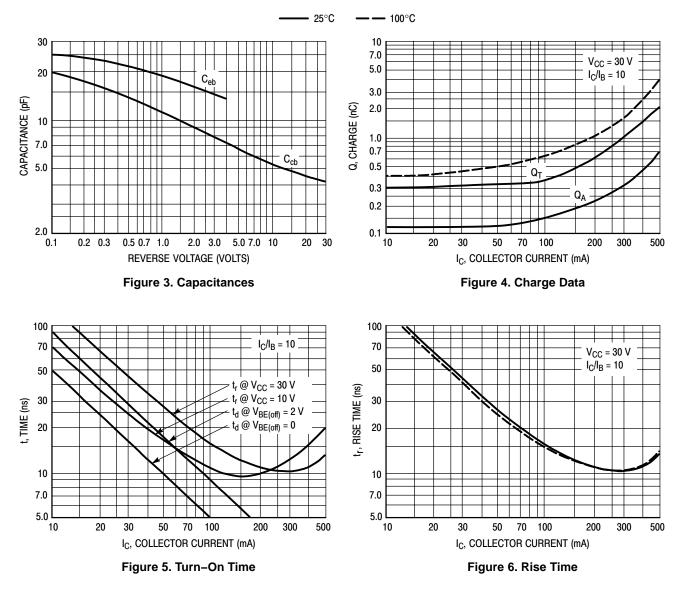


Figure 1. Turn–On Time

Figure 2. Turn-Off Time

TRANSIENT CHARACTERISTICS



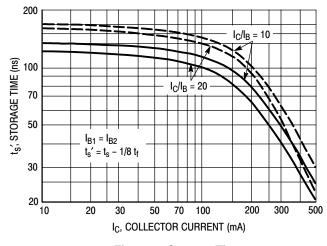
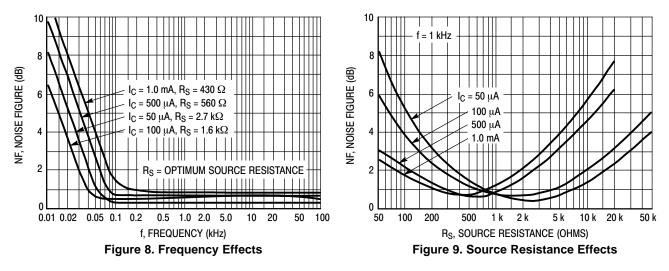


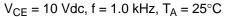
Figure 7. Storage Time

SMALL-SIGNAL CHARACTERISTICS NOISE FIGURE

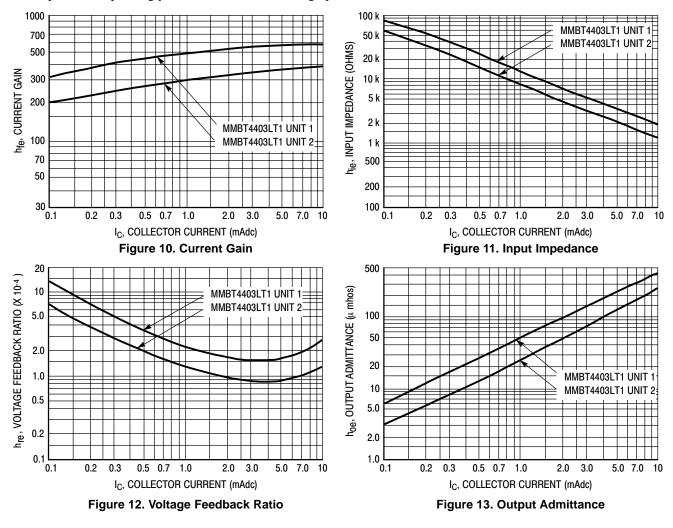
 $V_{CE} = -10$ Vdc, $T_A = 25^{\circ}C$; Bandwidth = 1.0 Hz



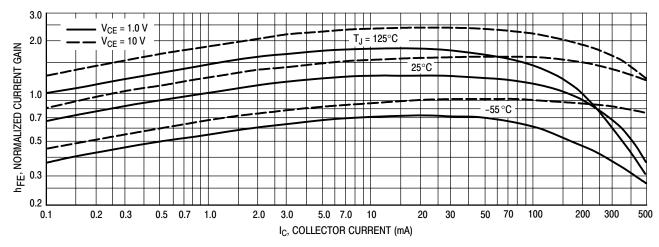
h PARAMETERS



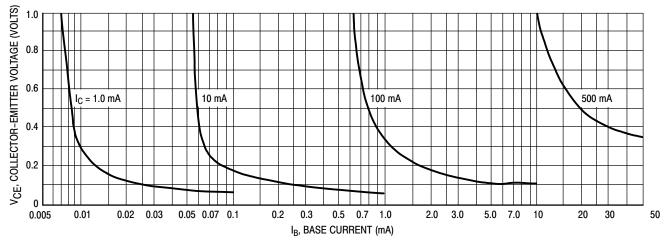
This group of graphs illustrates the relationship between h_{fe} and other "h" parameters for this series of transistors. To obtain these curves, a high–gain and a low–gain unit were selected from the MMBT4403LT1 lines, and the same units were used to develop the correspondingly numbered curves on each graph.

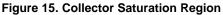












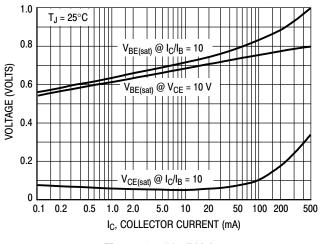
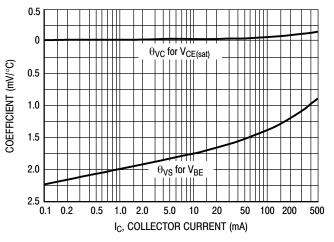


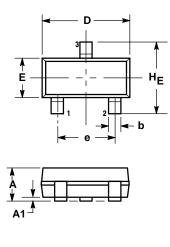
Figure 16. "On" Voltages

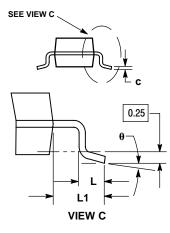




PACKAGE DIMENSIONS

SOT-23 (TO-236) CASE 318-08 **ISSUE AN**





NOTES: 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. 2. CONTROLLING DIMENSION: INCH. 3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD

THICKNESS IS THE MINIMUM THICKNESS OF

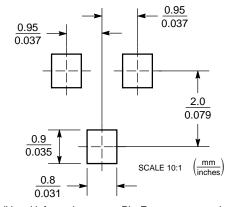
	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α	0.89	1.00	1.11	0.035	0.040	0.044
A1	0.01	0.06	0.10	0.001	0.002	0.004
b	0.37	0.44	0.50	0.015	0.018	0.020
С	0.09	0.13	0.18	0.003	0.005	0.007
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
е	1.78	1.90	2.04	0.070	0.075	0.081
L	0.10	0.20	0.30	0.004	0.008	0.012
L1	0.35	0.54	0.69	0.014	0.021	0.029
HE	2.10	2.40	2.64	0.083	0.094	0.104

STYLE 6:

PIN 1. BASE EMITTER 2.

3. COLLECTOR

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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